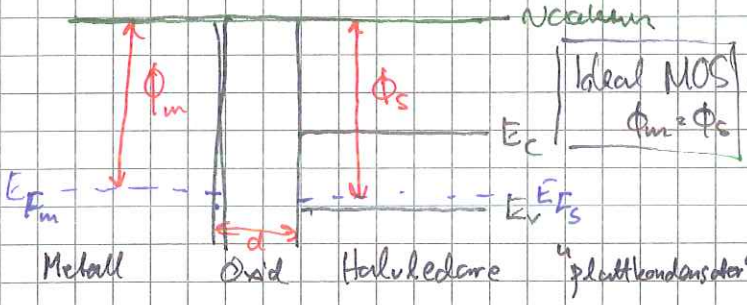
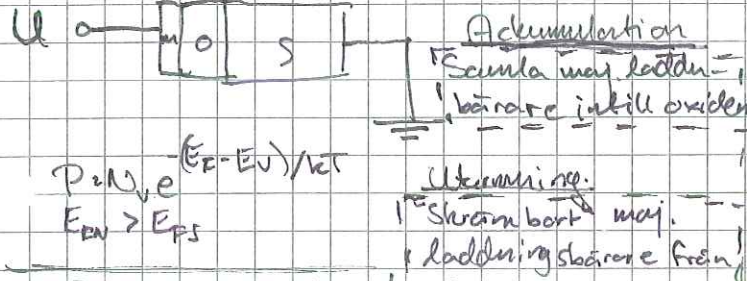


MOS: Metal-Oxide-Semiconductor



$V_{in} \approx 0$ P-MOS $U_g < U_{substrat}$.
 P-MOS leder: $V_{out} = U_{DD} = 5V$
 (N-MOS stängd).
 $V_{in} = 5V$ PMOS stängd.
 NMOS leder $\Rightarrow V_{out} = 0$.

DIBL - Drain-Induced Barrier Lowering



CCD: Charged Coupled Device
 djup utvärmsing.
 Snabbt gå mot inversion tar "en sekund" att konstigt generera e^- intill oxiden.
 $\sim 1s$

Inversion:
 byt ledna bärare till ytan.
 $n_s = N_C e^{-(E_{FS} - E_F)/kT}$

